1-BIT TO 2-BIT ADDRESS DRIVER WITH 3-STATE OUTPUTS

SCES082G – AUGUST 1996 – REVISED JUNE 1999

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Output Ports Have Equivalent 26-Ω Series Resistors, So No External Resistors Are Required**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Packaged in Thin Very Small-Outline Package**

NOTE: For tape and reel order entry:
The DBBR package is abbreviated to GR.

DBB PACKAGE
(TOP VIEW)

2Y2	1	80	1Y3
1Y2	2	79	2Y3
GND	3	78	GND
2Y1	4	77	1Y4
1Y1	5	76	2Y4
V_{CC}	6	75	V_{CC}
A1	7	74	1Y5
A2	8	73	2Y5
GND	9	72	GND
A3	10	71	1Y6
A4	11	70	2Y6
GND	12	69	GND
A5	13	68	1Y7
A6	14	67	2Y7
V_{CC}	15	66	V_{CC}
A7	16	65	1Y8
A8	17	64	2Y8
GND	18	63	GND
A9	19	62	1Y9
$\overline{OE1}$	20	61	2Y9
$\overline{OE2}$	21	60	1Y10
A10	22	59	2Y10
GND	23	58	GND
A11	24	57	1Y11
A12	25	56	2Y11
V_{CC}	26	55	V_{CC}
A13	27	54	1Y12
A14	28	53	2Y12
GND	29	52	GND
A15	30	51	1Y13
A16	31	50	2Y13
GND	32	49	GND
A17	33	48	1Y14
A18	34	47	2Y14
V_{CC}	35	46	V_{CC}
2Y18	36	45	1Y15
1Y18	37	44	2Y15
GND	38	43	GND
2Y17	39	42	1Y16
1Y17	40	41	2Y16

description

This 1-bit to 2-bit address driver is designed for 1.65-V to 3.6-V V_{CC} operation.

Active bus-hold circuitry is provided to hold unused or floating inputs at a valid logic level.

The outputs, which are designed to sink up to 12 mA, include equivalent 26-Ω resistors to reduce overshoot and undershoot.

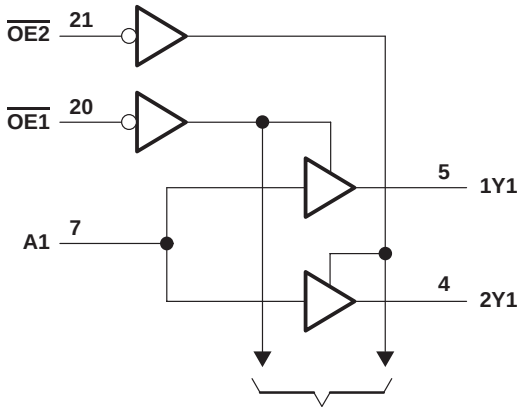
To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74ALVCH162830 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

INPUTS			OUTPUTS	
$\overline{OE1}$	$\overline{OE2}$	A	1Yn	2Yn
L	H	H	H	Z
L	H	L	L	Z
H	L	H	Z	H
H	L	L	Z	L
L	L	H	H	H
L	L	L	L	L
H	H	X	Z	Z

logic diagram (positive logic)



To 17 Other Channels

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0) . . . . . –50 mA
Continuous output current, I_O . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3) . . . . . 106°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		1.65	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 1.65 V to 1.95 V	$0.65 \times V_{CC}$		V
		V_{CC} = 2.3 V to 2.7 V	1.7		
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 1.65 V to 1.95 V		$0.35 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V		0.7	
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 1.65 V		–2	mA
		V_{CC} = 2.3 V		–6	
		V_{CC} = 2.7 V		–8	
		V_{CC} = 3 V		–12	
I_{OL}	Low-level output current	V_{CC} = 1.65 V		2	mA
		V_{CC} = 2.3 V		6	
		V_{CC} = 2.7 V		8	
		V_{CC} = 3 V		12	
$\Delta t/\Delta v$	Input transition rise or fall rate			10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		1.65 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –2 mA		1.65 V	1.2			
		I_{OH} = –4 mA		2.3 V	1.9			
		I_{OH} = –6 mA		2.3 V	1.7			
				3 V	2.4			
		I_{OH} = –8 mA		2.7 V	2			
		I_{OH} = –12 mA		3 V	2			
V_{OL}		I_{OL} = 100 µA		1.65 V to 3.6 V			0.2	V
		I_{OL} = 2 mA		1.65 V			0.45	
		I_{OL} = 4 mA		2.3 V			0.4	
		I_{OL} = 6 mA		2.3 V			0.55	
				3 V			0.55	
		I_{OL} = 8 mA		2.7 V			0.6	
		I_{OL} = 12 mA		3 V			0.8	
I_I		$V_I = V_{CC}$ or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.58 V		1.65 V	25			µA
		V_I = 1.07 V		1.65 V	–25			
		V_I = 0.7 V		2.3 V	45			
		V_I = 1.7 V		2.3 V	–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V		3 V	–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}		$V_O = V_{CC}$ or GND		3.6 V			±10	µA
I_{CC}		$V_I = V_{CC}$ or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	$V_I = V_{CC}$ or GND		3.3 V		4.5		pF
	Data inputs					5		
C_o	Outputs	$V_O = V_{CC}$ or GND		3.3 V		7.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current. It is the minimum overdrive current required to switch the input from one state to another.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 1.8 V	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			TYP	MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	Y	§	1.2	3.8		4	1.7	3.5	ns
t_{en}	$\overline{OE}$	Y	§	1	5.7		5.7	1	4.8	ns
t_{dis}	$\overline{OE}$	Y	§	1.5	6.2		5.4	1.7	5.2	ns

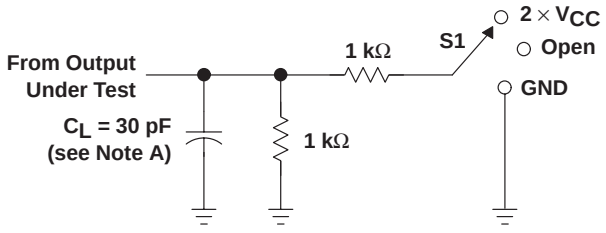
§ This information was not available at the time of publication.

operating characteristics, $T_A = 25°C$

PARAMETER			TEST CONDITIONS	V_{CC} = 1.8 V	V_{CC} = 2.5 V	V_{CC} = 3.3 V	UNIT
				TYP	TYP	TYP	
C_{pd}	Power dissipation capacitance	All outputs enabled	C_L = 0, f = 10 MHz	†	50	54	pF
		All outputs disabled		†	8	8	

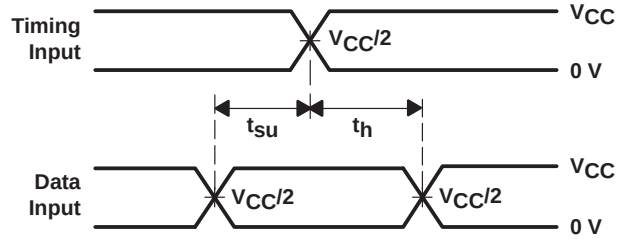
† This information was not available at the time of publication.

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 1.8 V

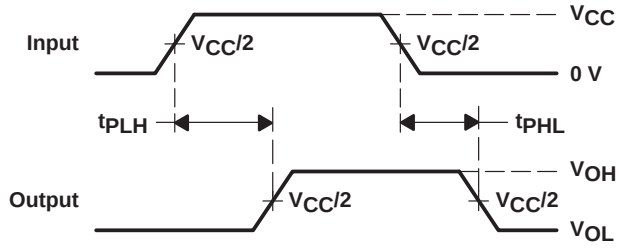


LOAD CIRCUIT

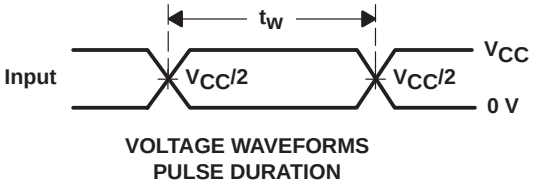
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



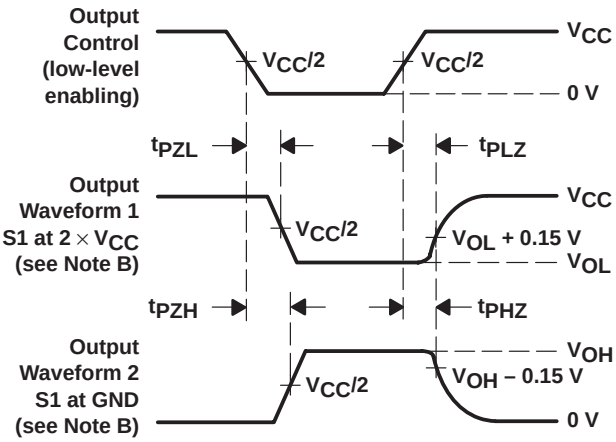
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

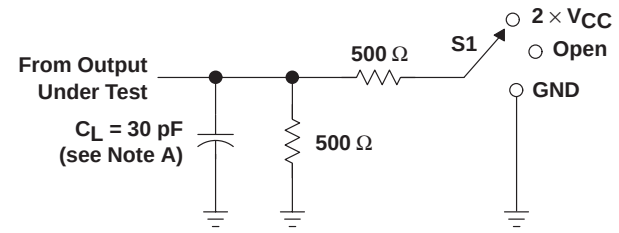


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

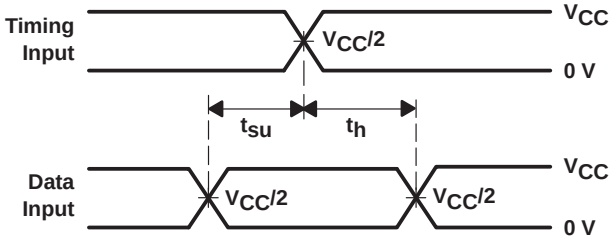
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

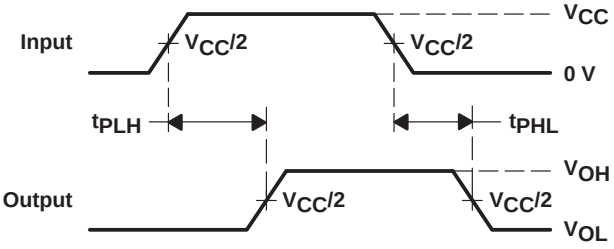


TEST	S1
t_{pd} t_{PLZ}/t_{PZL} t_{PHZ}/t_{PZH}	Open 2 × V_{CC} GND

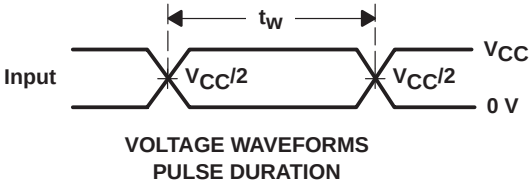
LOAD CIRCUIT



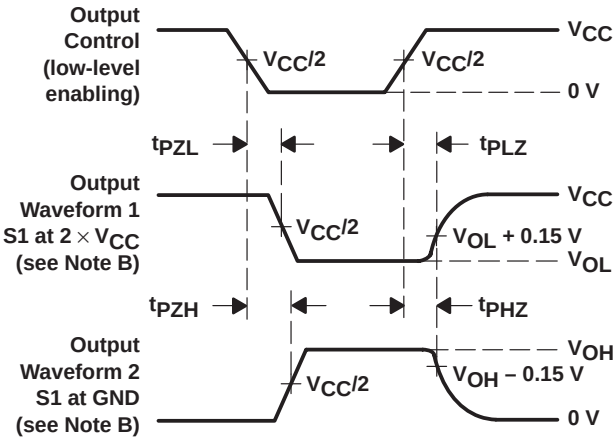
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

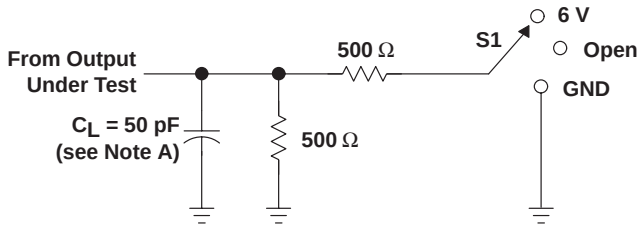


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

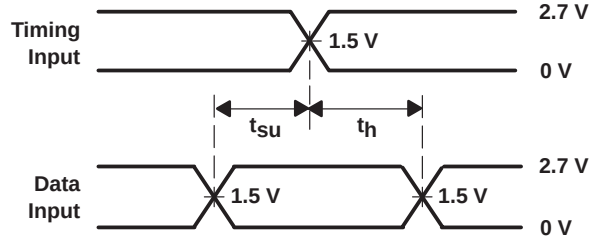
Figure 2. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

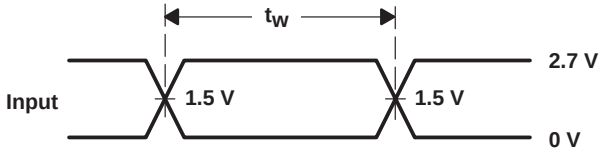


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

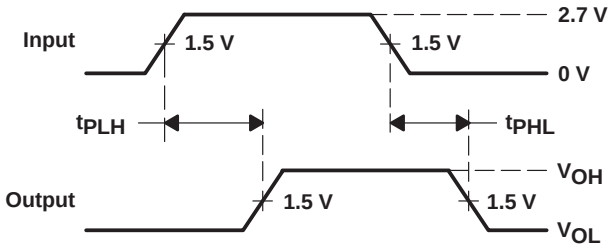
LOAD CIRCUIT



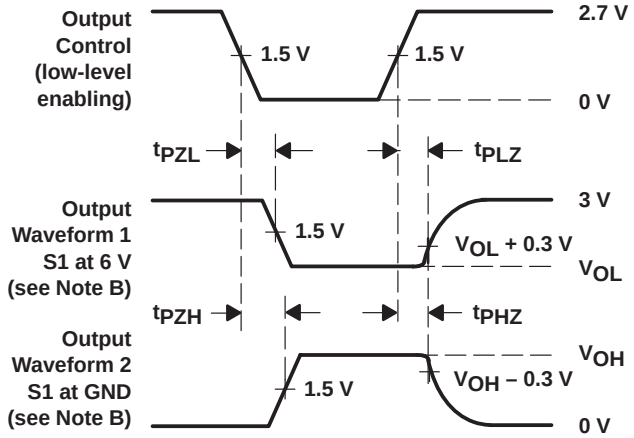
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



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F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 3. Load Circuit and Voltage Waveforms

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